

**AMENDMENTS TO THE SPECIFICATION**

At page 2, before "BACKGROUND OF THE INVENTION", please insert the following new paragraph:

This application is a divisional of Application No. 09/585,428, filed June 2, 2000, the subject matter of which is incorporated by reference herein.

Replace paragraph beginning on line 16, page 54:

As the glass layer 7, SW-3 made by Asahi Techno Glass Corporation (Iwaki IWAKI Glass) or the like may also be used, in the above-described embodiment.

Replace paragraph beginning on line 6, page 58:

As the glass layer 7, SW-3 made by Asahi Techno Glass Corporation (Iwaki IWAKI Glass) or the like may also be used, in the above-described embodiment.

Replace paragraph beginning on line 23, page 61:

As the glass layer 7, SW-3 made by Asahi Techno Glass Corporation (Iwaki IWAKI Glass) or the like may also be used, in the above-described embodiment.

Replace paragraph beginning on line 8, page 64:

As the glass layer 7, SW-3 made by Asahi Techno Glass Corporation (Iwaki IWAKI Glass) or the like may also be used, in the above-described embodiment.

Replace paragraph beginning on line 14, page 65:

As the glass layer 7, SW-3 made by Asahi Techno Glass Corporation (Iwaki IWAKI Glass) or the like may also be used, in ~~the~~ this embodiment.

Replace paragraph beginning on line 16, page 67:

As the glass layer 7, SW-3 made by Asahi Techno Glass Corporation (Iwaki IWAKI Glass) or the like may also be used, in the above-described embodiment.

Replace paragraph beginning on line 17, page 73:

As the glass layer 7, SW-3 made by Asahi Techno Glass Corporation (Iwaki IWAKI Glass) or the like may also be used, in the above-described embodiment.

Replace paragraph beginning on line 13, page 75:

As the glass layer 7, SW-3 made by Asahi Techno Glass Corporation (Iwaki IWAKI Glass) or the like may also be used, in the above-described embodiment.

Replace paragraph beginning on line 19, page 78:

As the glass layer 7, SW-3 made by Asahi Techno Glass Corporation (Iwaki IWAKI Glass) or the like may also be used, in the above-described embodiment.

Replace paragraph beginning on line 13, page 79:

As the glass layer 7, SW-3 made by Asahi Techno Glass Corporation (Iwaki IWAKI Glass) or the like may also be used, in each of these embodiments.

Replace paragraph beginning on line 4, page 80:

As the glass layer 7, SW-3 made by Asahi Techno Glass Corporation (Iwaki IWAKI Glass) or the like may also be used, in this embodiment.

Replace paragraph beginning on line 14, page 80 and bridging with page 81:

Further, in each embodiment described above, a glass layer 7 is bonded to a single-crystal Si layer 4. However, it is also possible that a non-light-transmitting-property substrate having a hole transmitting light at a position corresponding to a hole 6, 6a formed in a single-crystal Si layer is bonded to the single-crystal Si layer 4. For example, as shown in FIGS. 27A through 27F, after a hole 6 is formed in a single-crystal Si layer 4, a non-light-transmitting-property substrate 82 having a hole 81 formed therein at a predetermined position previously is bonded to the single-crystal Si layer 4. Any material such as metal, ceramic, resin, non-light-transmitting glass, or the like can be employed as a material of this non-light-transmitting-property substrate 82 as long as it can be bonded to the single-crystal Si layer 4. SW-3 made by Asahi Techno Glass Corporation (Iwaki IWAKI Glass) or the like may also be used as the glass layer 7. Further, any of various bonding methods described above as well as anodic bonding can be employed as a bonding method. Then, the single-crystal Si substrate 2 and SiO<sub>2</sub>

layer 3 are removed, and a thus-obtained combination is cut to a desired size, and, thus, an optical-pickup slider is completed.

Replace paragraph beginning on line 18, page 135 and bridging with page 136:

Further, although, as a glass substrate 2104 having a property of transmitting light, #7740 made by Corning Incorporated and SW-3 made by Asahi Techno Glass Corporation (Iwaki IWAKI Glass) were mentioned, another substrate may be used instead. Specifically, when the above-described direct bonding in normal temperature is used, a quarz quartz substrate or light-transmitting resin can be used. In particular, in a case where quarz quartz is used, it is possible to bond a light-transmitting-property substrate and an Si layer together by direct bonding in a high temperature. In this method, a surface of the substrate is sufficiently cleaned, dusts and stains on the surface are removed and the surface is dried. Then, the surfaces are caused to come into contact with one another in a normal atmosphere. Then, heat treatment or anneal at higher than 900 °C is performed in a nitrogen gas. Thereby, the substrate is bonded.